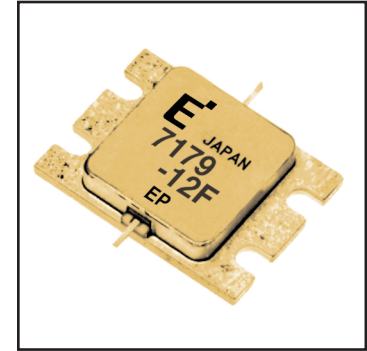


FEATURES

- High Output Power: $P_{1dB} = 41.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.0\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 38\%$ (Typ.)
- Low $IM_3 = -46\text{dBc}$ @ $P_o = 30.5\text{dBm}$
- Broad Band: 7.1 ~ 7.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



DESCRIPTION

The FLM7179-12F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ\text{C}$	57.6	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -5.6 mA respectively with gate resistance of 50Ω .

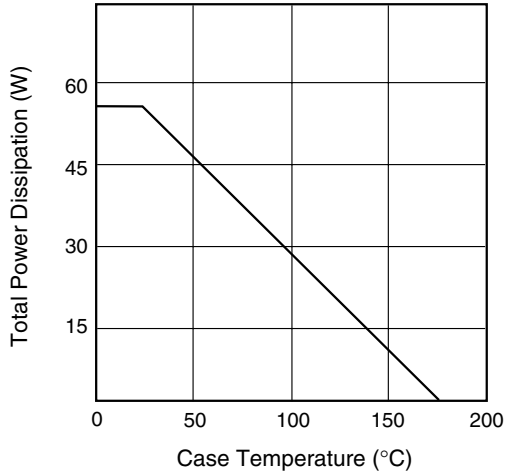
ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	5000	7500	mA
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 3250\text{mA}$	-	5000	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 250\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -250\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65I_{DSS}$ (Typ.), $f = 7.1 \sim 7.9\text{GHz},$ $Z_S = Z_L = 50\text{ohm}$	40.5	41.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.0	9.0	-	dB
Drain Current	I_{dsr}		-	3250	4000	mA
Power-added Efficiency	η_{add}		-	38	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3		$f = 7.9\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 30.5\text{dBm}$ S.C.L.	-44	-46	-
Thermal Resistance	R_{th}	Channel to Case	-	2.3	2.6	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	ΔT_{ch}	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

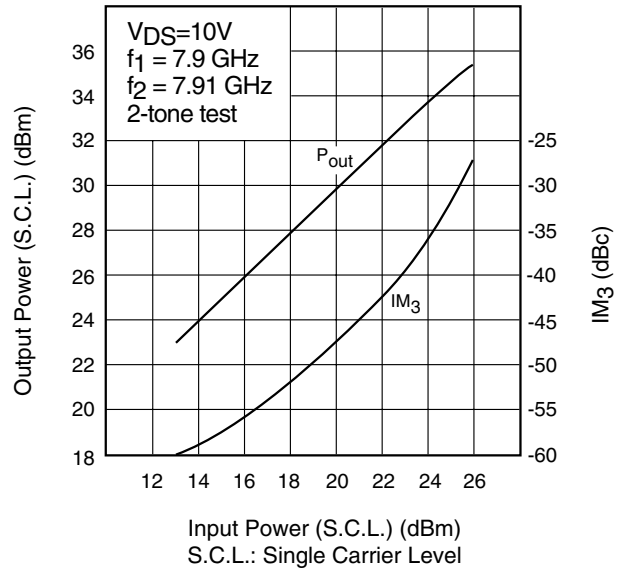
CASE STYLE: IK

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

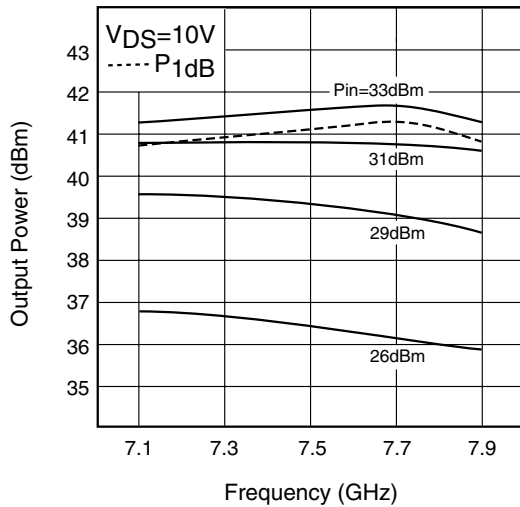
POWER DERATING CURVE



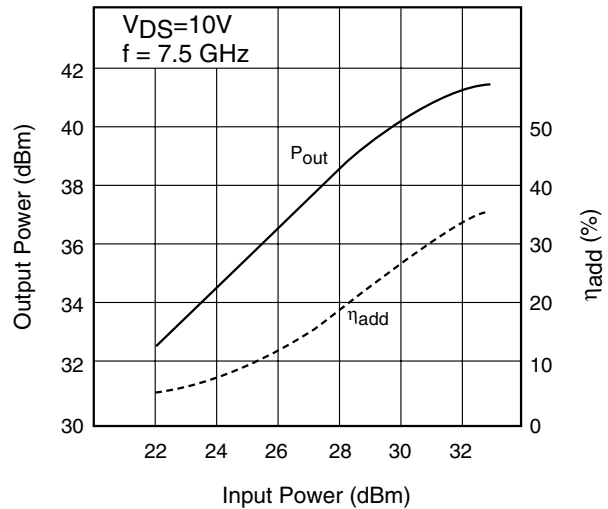
OUTPUT POWER & IM₃ vs. INPUT POWER

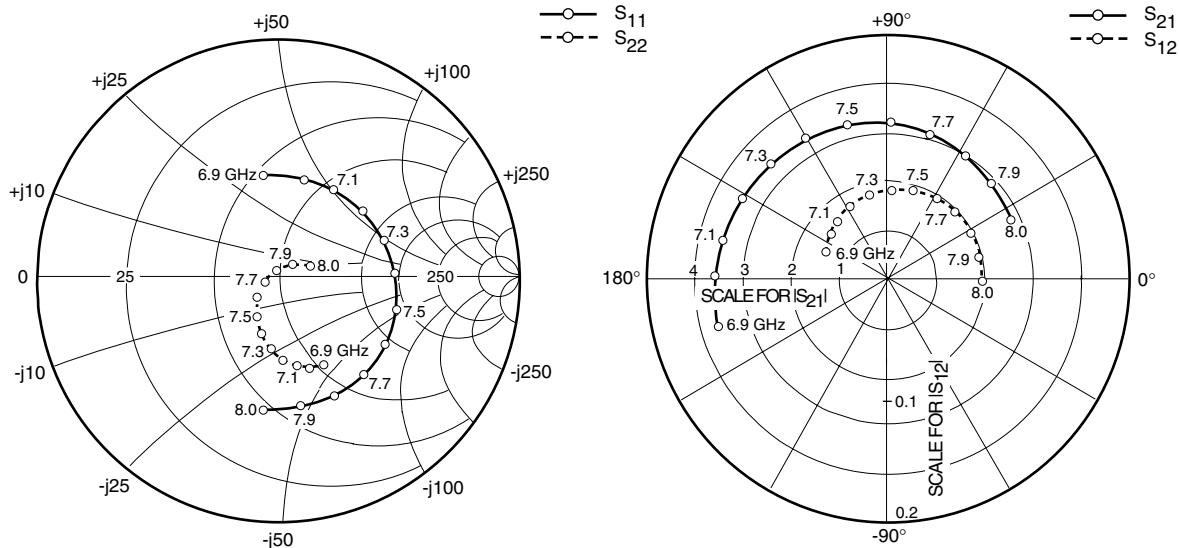


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





S-PARAMETERS

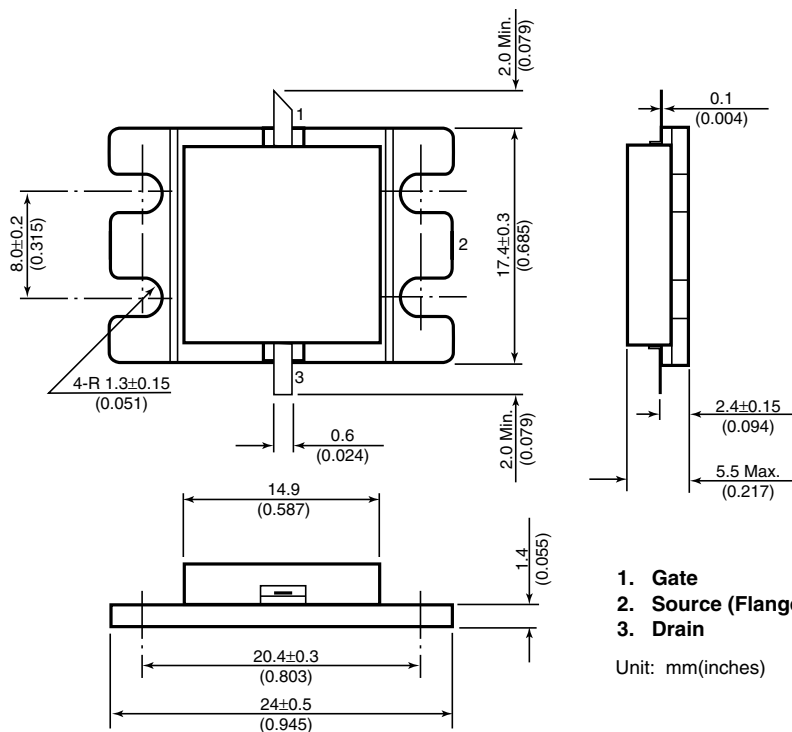
$V_{DS} = 10V, I_{DS} = 3250mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6900	.425	99.1	3.694	-164.7	.056	156.4	.408	-64.4
7000	.418	76.0	3.616	179.1	.060	141.9	.398	-72.6
7100	.424	58.4	3.553	167.2	.063	131.9	.378	-78.5
7200	.439	38.0	3.477	151.7	.067	118.1	.347	-86.9
7300	.460	19.0	3.409	136.2	.072	101.9	.304	-96.1
7400	.483	0.7	3.336	120.6	.074	88.1	.252	-106.9
7500	.502	-16.4	3.262	104.8	.077	73.5	.190	-118.4
7600	.520	-33.0	3.180	89.3	.077	59.3	.127	-133.2
7700	.535	-49.4	3.094	73.5	.079	44.3	.062	-154.6
7800	.546	-65.3	3.007	57.6	.078	28.8	.023	107.8
7900	.554	-80.8	2.913	41.8	.078	12.6	.073	40.9
8000	.560	-96.4	2.819	25.7	.078	-1.3	.129	18.5

FLM7179-12F

C-Band Internally Matched FET

Case Style "IK" Metal-Ceramic Hermetic Package



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CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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